

In the Specification:

Please amend the Specification as follows:

Please replace the paragraph beginning on page 1, line 3, with the following rewritten paragraph:

The present invention ~~related~~relates to an active matrix type liquid crystal display provided with a thin film transistor (hereinafter, referred to as TFT) as a switching element, and specifically relates to the liquid crystal display provided with an electrostatic protection element protecting the TFT formed on a substrate on an array side and areas between bus lines from a destruction or a shortage due to static electricity.

Please replace the paragraph beginning on page 1, line 12, with the following rewritten paragraph:

The active matrix type LCD is widely used in computers or equipment for the use of OA (Office Automation) as a flat panel display providing superior picture quality. In this active matrix type LCD, a voltage is applied ~~electrode~~ from both electrodes to a liquid crystal layer sealed between the substrate on the array side forming a TFT and pixel electrode and an opposing substrate forming common, thereby driving the liquid crystal display.

Please replace the paragraph beginning on page 1, line 20, with the following rewritten paragraph:

A plurality of gate bus lines to which a scanning signal is sequentially input to select a driving display pixel are formed in parallel to each other on the substrate on the array side. Further, an insulation film is formed on the plurality of gate bus lines, and a plurality of data bus lines ~~in~~-substantially orthogonal to the gate bus lines are formed on an insulation film. Each area decided by the plurality of gate bus lines and the plurality of data bus lines formed ~~in~~-orthogonal to each other in a matrix shape becomes a pixel area, and the TFT and the display electrode are formed in each pixel area. A gate electrode of the TFT is connected to a predetermined gate bus line, a drain electrode is connected to a predetermined data bus line, and a source electrode is connected to the display electrode in the pixel area.

Please replace the paragraph beginning on page 4, line 4, with the following rewritten paragraph:

However, according to this method, in order to obtain a higher resistance using ITO, an area is required to secure ~~to lengthen~~ the distance of the zigzag-shape. Thus, a problem that an external size of the panel becomes large exists.

Please replace the paragraph beginning on page 7, line 13, with the following rewritten paragraph:

Also, based on the previous fabrication experiences, obstacles due to static electricity are known to ~~be occurred~~occur by sharp pulse-like static electricity at extremely high voltage for a short period of time and static electricity continuously applied to each

element for a long period of time even if the voltage is relatively low. Therefore, although the electrostatic protection circuit described in the publication of Japanese Laid Open Patent Application No. 10-303431 can be expected to be effective in the former case, little result is expected in the latter case as the path for the current to escape is cut off when the voltage is reduced to a certain extent. Further, according to the electrostatic protection circuit described in the above publication, since the current due to static electricity all flows in the first TFT, the redundancy is poor and the load is exceedingly increased, therefore the possibility of the first TFT ~~to be~~ being destroyed exists. Furthermore, since the gate electrode (G) of the second TFT 532 is directly connected with the external output electrode 502 of the bus line and the gate electrode (G) of the third TFT 534 is directly connected with the short ring 506, the redundancy against shortage is reduced.

Please replace the paragraph beginning on page 8, line 2, with the following rewritten paragraph:

As still another conventional electrostatic protection circuit, there is a structure shown in Fig. 31, which is described in the publication of Japanese Laid Open Patent Application No. 7-60875. This is an electrostatic protection circuit connecting between the bus line 504 and the short ring 506 via a resistive component by a two-way transistor using non-linear elements 402 and 404. Besides the two-way transistor, a non-linear element such as a ~~shot key~~ Schottky diode, which can be a resistive component, may be also used. Since the resistive component by the non-linear element has a sufficient high resistive component so as

not to affect the operation of each bus line, the resistive component by the non-linear element can be ~~remained~~remain after the panel is completed. Further, as to static electricity, since some current which can disperse electric ~~charges~~charge flows, the resistive component ~~by~~of the non-linear element functions as an anti-electrostatic element.

Please replace the paragraph beginning on page 16, line 11, with the following rewritten paragraph:

According to the present invention, the contact holes are formed on the protection film on the gate bus line or the data (drain) bus line and the short ring and each of the bus lines are electrically connected via the contact holes. A contact resistance generated between different metals (for example, Ti and ITO) in this structure can obtain the ohmic contact by selecting materials and the resistance value of the resistive component can also be controlled by the number or the size of the contact holes, or by the subsequent treatment processes for the underlying metal. The metal contact is certainly not limited to the ohmic contact and a resistive device having a non-linear characteristic can be arranged by the ~~shot-key~~Schottky connection.

Please replace the paragraph beginning on page 50, line 15, with the following rewritten paragraph:

Next, as shown in (e) of Fig. 25, the ITO layer 43 is formed by patterning the ITO when forming the display electrode so that the adjacent metal layers 200, 202 and the

like are electrically connected via the contact hole 98. At this time, since an ITO layer 43a and the Al layer of the metal layer 200d form a shot keySchottky connection and the ring-shaped Ti layer ~~remained~~remaining in the contact hole 98 and an ITO layer 43b form an ohmic connection, an overall contact resistance can be increased. ~~for~~For example, when the drain metal is Ti(20nm)/Al(75nm)/Ti(20nm), the contact resistance per a contact hole on the metal layer 200d is equal to 35 to 36k $\Omega$  and if 3 or 4 of the metal layers 200d are serially connected, a state possible for the array inspection can be obtained.